30V N-Channel Enhancement Mode MOSFET

Description

The YXD3400NE1 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and high density cell Design for ultra low on-resistance. This device is suitable for use as a load switch or in PWM applications.

General Features

- V_{DS} =30V，I_D =5.8A
  $R_{DS(ON)}$(Typ.)=30mΩ @V_{GS}=2.5V
  $R_{DS(ON)}$(Typ.)=24mΩ @V_{GS}=4.5V
- High power and current handing capability
- Lead free product is acquired
- Surface mount package

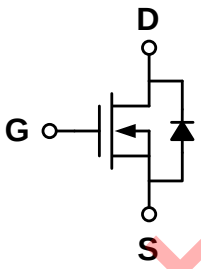
Application

- PWM applications
- Load switch

Package

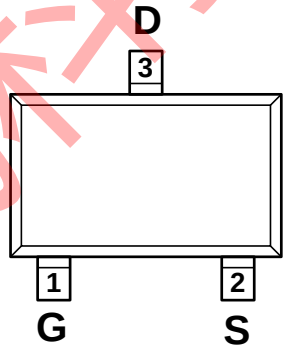
- SOT-23

Schematic diagram



Marking and pin assignment

SOT-23
(TOP VIEW)



Ordering Information

Part Number	Storage Temperature	Package	Devices Per Reel
YXD3400NE1	-55°C to +150°C	SOT-23	3000

Absolute Maximum Ratings (TA=25℃ unless otherwise noted)

parameter	symbol	limit	unit
Drain-source voltage	V_{DS}	30	V
Gate-source voltage	V_{GS}	±12	V
Drain current-continuous[a]@Tj=125℃	I_D	5.8	A
-pulse *d*[b]	I_{DM}	23	A
Drain-source Diode forward current	Is	0.6	A
Maximum power dissipation	P_D	0.7	W
Operating junction Temperature range	Tj	-55—150	℃

Electrical Characteristics (TA=25℃ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
OFF Characteristics						
Drain-source breakdown voltage	BV_{DSS}	V_{GS}=0V, I_D=250μA	30	-	-	V
Zero gate voltage drain current	I_{DSS}	V_{DS}=30V, V_{GS}=0V	-	-	1	μA
Gate-body leakage	I_{GSS}	V_{DS}=0V, V_{GS}=±12V	-	-	±100	nA
ON Characteristics						
Gate threshold voltage	$V_{GS(th)}$	V_{DS}=V_{GS}, I_D=250μA	0.5	0.9	1.5	V
Drain-source on-state resistance	$R_{DS(ON)}$	V_{GS}=4.5V, I_D=5A	-	24	30	mΩ
		V_{GS}=2.5V, I_D=4A		30	45	
Forward transconductance	gfs	V_{GS}=5V, I_D=5.8A	-	33	-	S
Dynamic Characteristics						
Input capacitance	C_{ISS}	V_{DS}=15V ,V_{GS}=0V f=1.0MHz	-	630	-	pF
Output capacitance	C_{OSS}		-	76	-	
Reverse transfer capacitance	C_{RSS}		-	55	-	
Switching Characteristics						
Turn-on delay time	$t_{D(ON)}$	V_{DS}=15V V_{GS}=10V R_L=2.6 ohm R_{GEN}=3ohm	-	3	-	ns
Rise time	tr		-	2.5	-	
Turn-off delay time	$t_{D(OFF)}$		-	25	-	
Fall time	tf		-	4	-	
Total gate charge	Qg	V_{DS}=15V,I_D=5.8A V_{GS}=4.5V	-	6	-	nC
Gate-source charge	Qgs		-	1.3	-	
Gate-drain charge	Qgd		-	1.8	-	
DRAIN-SOURCE DIODE CHARACTERISTICS						
Diode forward voltage	V_{SD}	V_{GS}=0V,Is=1A	-	0.72	1.2	V

Notes:

a. surface mounted on FR4 board,t≤10sec

b. pulse test: pulse width≤300μs,duty≤2%

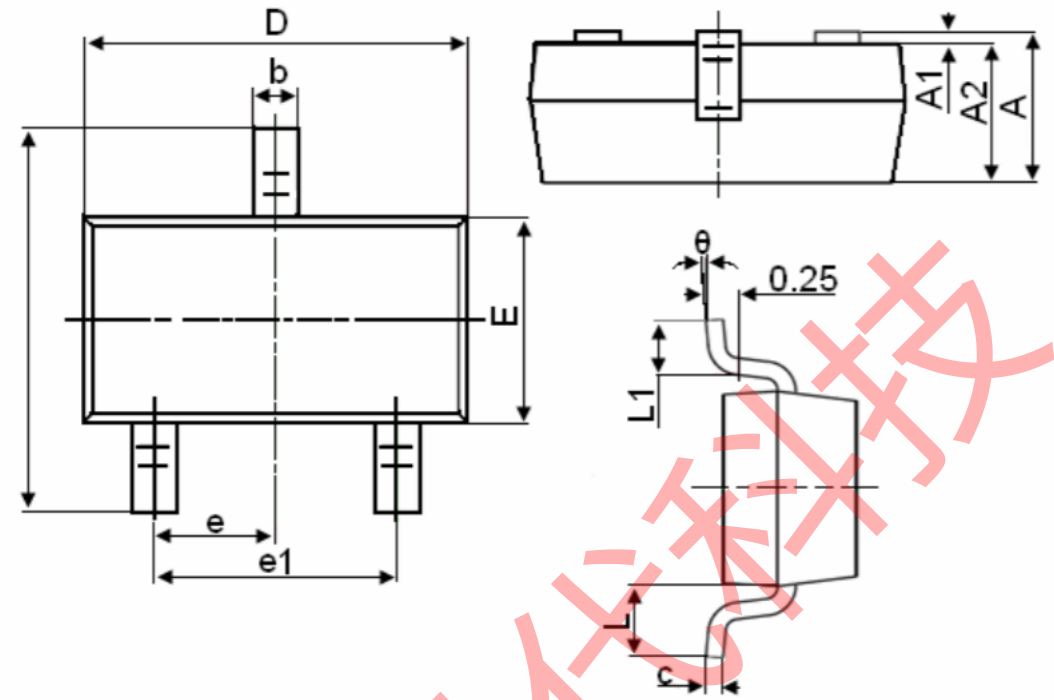
c. guaranteed by design, not subject to production testing

Thermal Characteristics

Thermal Resistance junction-to ambient	Rth JA	140	℃/W

Package Information

- **SOT-23**



Symbol	Dimensions in Millimeters	
	MIN.	MAX.
A	0.900	1.150
A1	0.000	0.100
A2	0.900	1.050
b	0.300	0.500
c	0.080	0.150
D	2.800	3.000
E	1.200	1.400
E1	2.250	2.550
e	0.950TYP	
e1	1.800	2.000
L	0.550REF	
L1	0.300	0.500
θ	0°	8°